IXYS

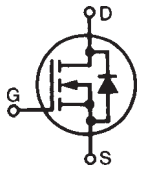
PolarHT™ Power MOSFET HiPerFET™

IXFC52N30P

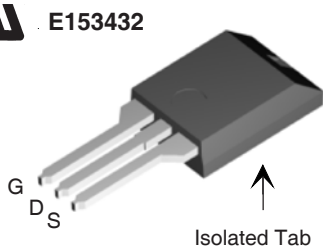
V_{DSS} = 300V
I_{D25} = 24A
$R_{DS(on)}$ ≤ 75mΩ
t_{rr} ≤ 200ns

(Electrically Isolated Back Surface)

N-Channel Enhancement Mode
Avalanche Rated



ISOPLUS 220™
E153432



G = Gate D = Drain
S = Source

Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		300	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ		300	V
V_{GSS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C		24	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}		150	A
I_A	T_C = 25°C		52	A
E_{AS}	T_C = 25°C		1	J
dV/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$		10	V/ns
P_D	T_C = 25°C		100	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6mm (0.062 in.) from case for 10s		300	°C
T_{SOLD}	Plastic body for 10s		260	°C
V_{ISOL}	50/60 Hz, RMS	t = 1min	2500	V~
	$I_{ISOL} \le$ 1mA	t = 1s	3000	V~
M_d	Mounting force		11..66 / 2.5..14.6	N/lb.
Weight			2	g

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)		Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250μA		300			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4mA		2.5		5.0	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V				±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$				25	μA
	V_{GS} = 0V	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 26A, Note 1				75	mΩ

Features

- UL recognized package
- Silicon chip on Direct-Copper-Bond substrate
  - High power dissipation
  - Isolated mounting surface
  - 2500V electrical isolation
- Avanlache rated
- Fast intrinsic diode

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor drives

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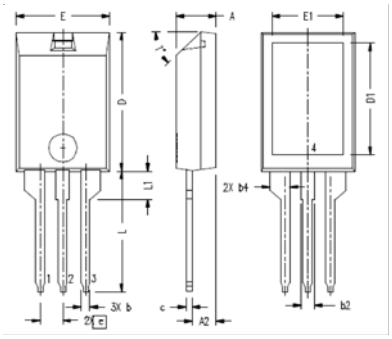
Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 26A, Note 1	20	30		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		3490		pF
C_{oss}			550		pF
C_{rss}			130		pF
$t_{d(on)}$	**Resistive Switching Times**		24		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 52A		22		ns
$t_{d(off)}$	R_G = 4Ω (External)		60		ns
t_f			20		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 26A		110		nC
Q_{gs}			25		nC
Q_{gd}			53		nC
R_{thJC}				1.25	°C/W
R_{thCS}			0.21		°C/W

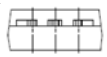
Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			52	A
I_{SM}	Repetitive, pulse width limited by T_{JM}			150	A
V_{SD}	I_F = 52A, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 25A, -di/dt = 100A/μs			200	ns
Q_{RM}	V_R = 100V, V_{GS} = 0V		800		nC
I_{RM}			7		A

Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

ISOPLUS220™ (IXFC) Outline





Note:
Bottom heatsink (Pin 4) is electrically isolated from Pin 1,2, or 3.

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55 BASIC	
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T°			42.5°	47.5°

Ref: IXYS CO 0177 R0

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ 25ºC

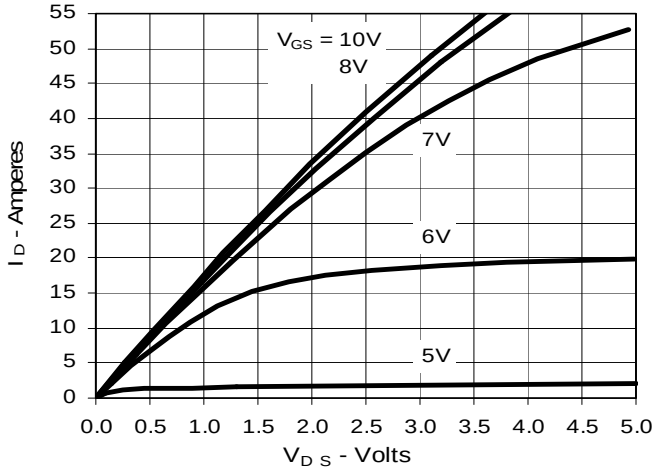


Fig. 2. Extended Output Characteristics @ 25ºC

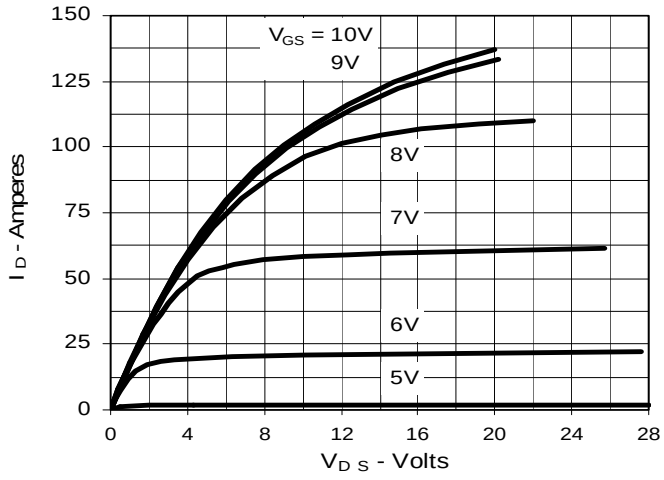


Fig. 3. Output Characteristics @ 125ºC

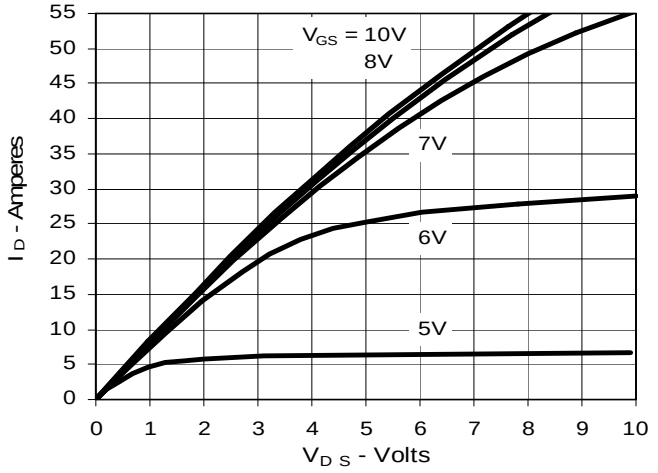


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 26A Value vs. Junction Temperature

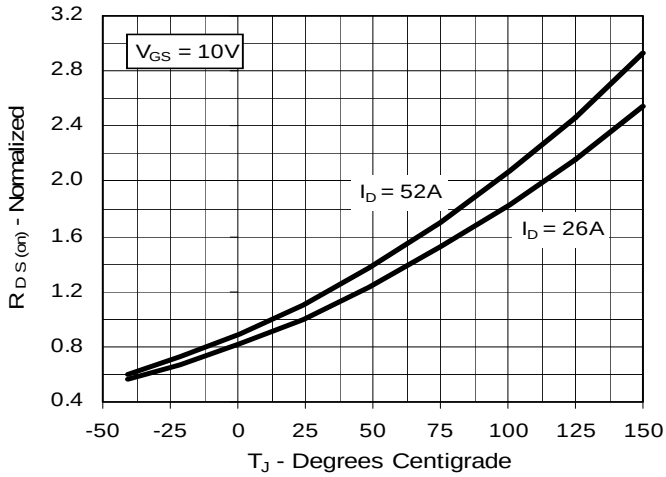


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 26A Value vs. Drain Current

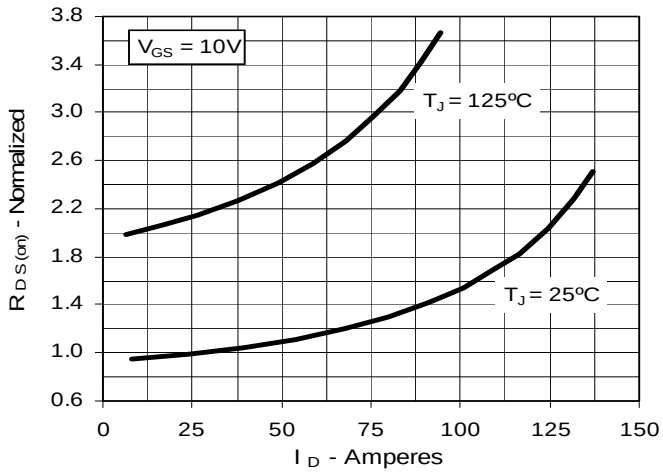


Fig. 6. Drain Current vs. Case Temperature

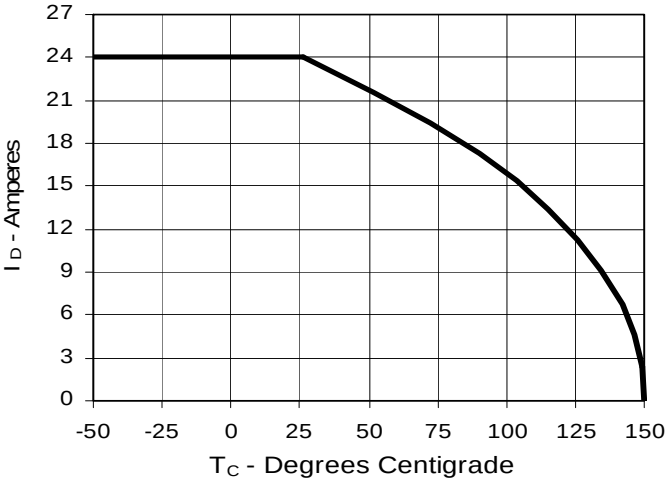


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Fig. 7. Input Admittance

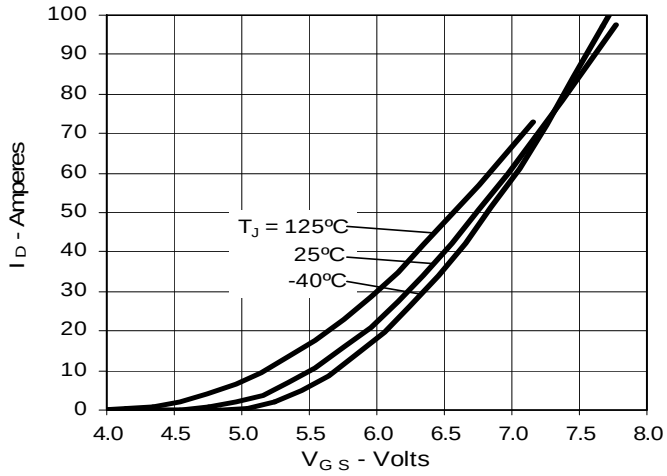

Fig. 8. Transconductance

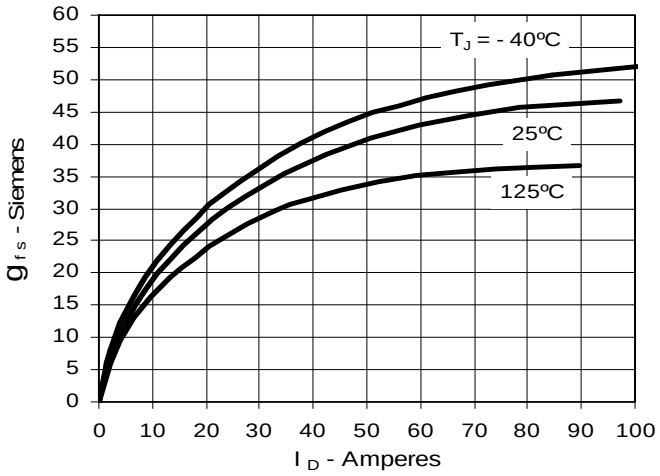

Fig. 9. Source Current vs. Source-To-Drain Voltage

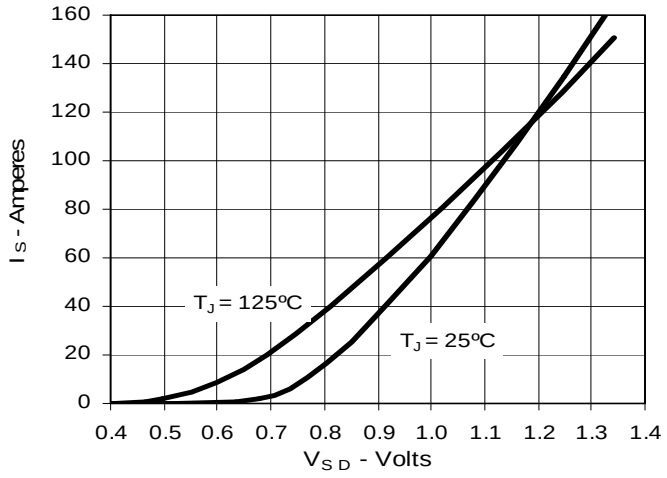

Fig. 10. Gate Charge

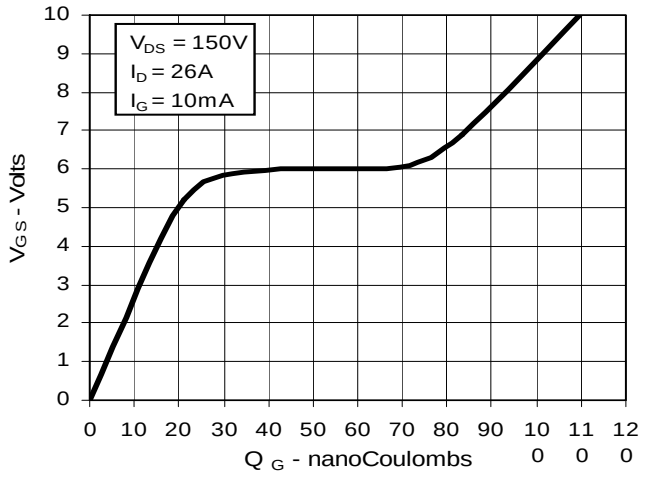

Fig. 11. Capacitance

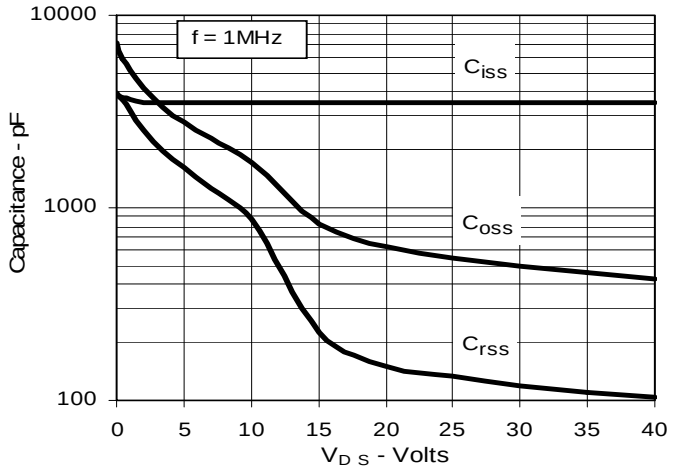

Fig. 12. Forward-Bias Safe Operating Area

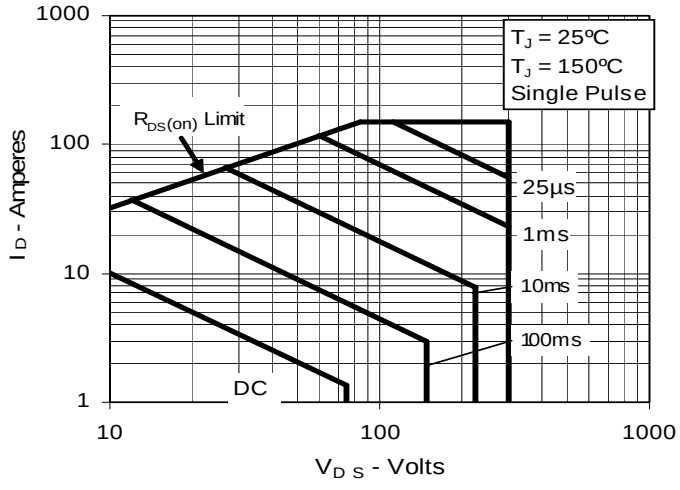

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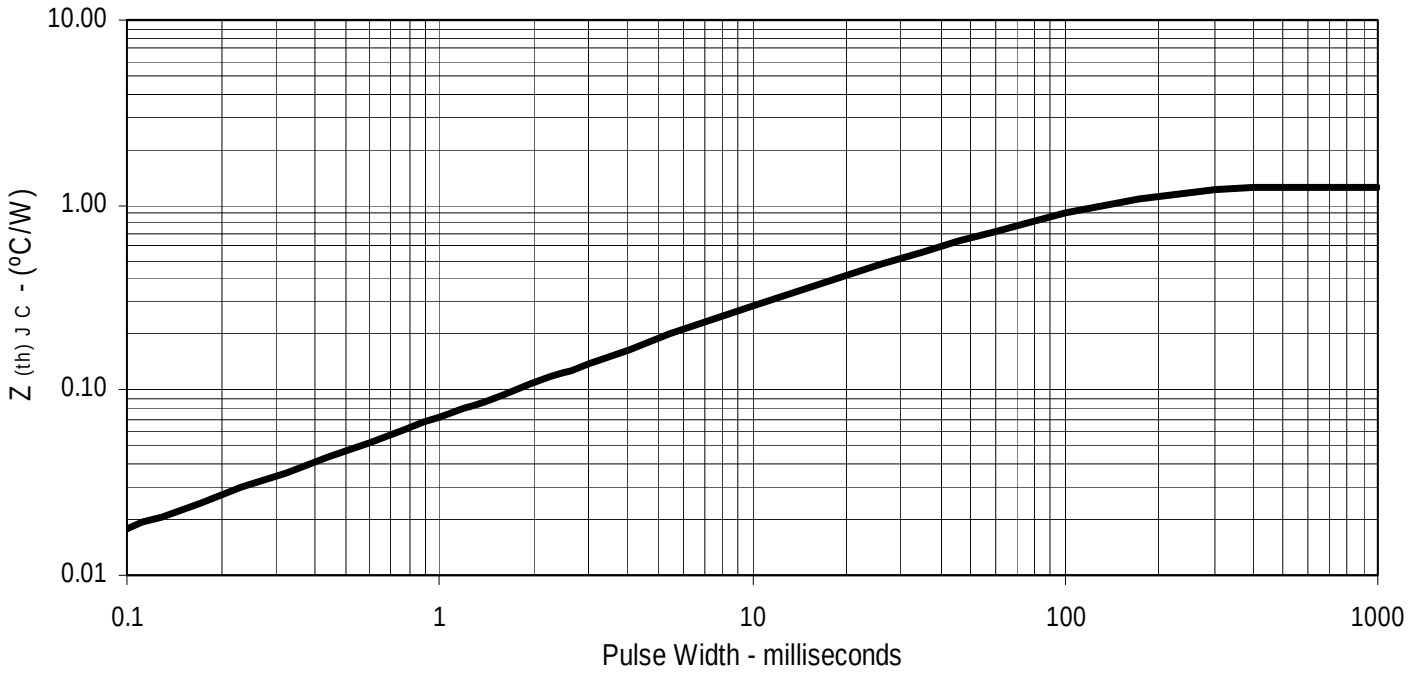
Fig. 13. Maximum Transient Thermal Impedance



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